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Data Sheet

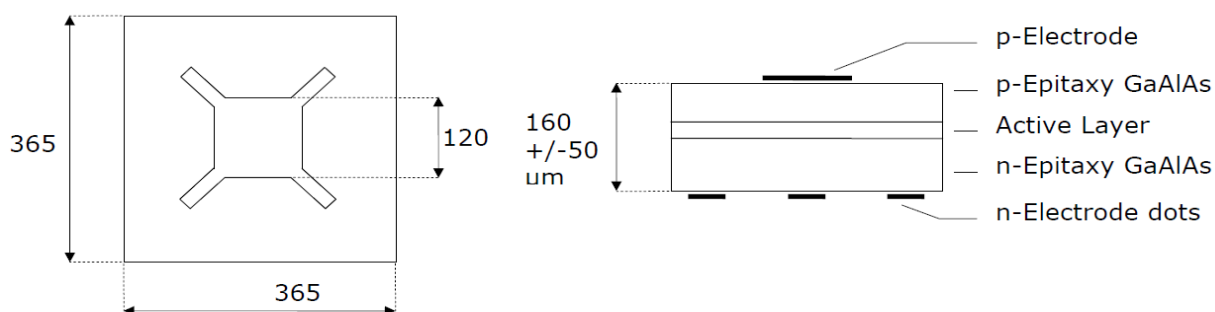
LED Chip Infrared

EOLC-875-17

Rev. 01, 2016

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	P (anode) up

Outlines (dimensions in microns)
Wire bond contacts can also be square



anode: gold alloy, thickness 1.5 μm ; cathode: gold alloy, thickness 0.5 μm , structured, 25% covered

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.5	V
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Radiant power ¹	$I_F = 20 \text{ mA}$	Φ_e	3	4		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	870	875	880	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		50		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		30; 25		ns

¹ Measured on bare chip on TO-18 header

Labeling

Type	Lot N°	Φ_e (typ) [mW]	V_F (typ) [V]	Quantity
EOLC-875-17				

Packing

Chips on adhesive film with wire-bond side top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.